Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

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Listing of Claims:

Claims 1 to 8. (Canceled)

Claims 9-11. (Withdrawn)

Claim 12. (Canceled)

Claim 13. (Currently Amended) A method of manufacturing a dopant-free single crystal of silicon carbide, comprising:

forming a single crystal of silicon carbide on a substrate surface at a temperature of not less than 900° C from an atmosphere containing a silicon carbide feedstock gas ~~comprising at least~~ consisting of a silicon source gas and a carbon source gas under the atmospheric condition of the partial pressure (ps) of the silicon source gas being held constant (at ps>0) and the partial pressure of the carbon source gas in the atmosphere repeatedly alternating between state pc1 present at an interval of time (tc1) and the state pc2 present at an interval of time (tc2) until the single crystal of silicon carbide is completely formed, where pc1>pc2 such that the partial pressure ratio (pc1/ps) falls within the range of 1-10 times the attachment coefficient ratio (Ss/Sc) and the partial pressure ratio (pc2/ps) falls within the range of less than ~~once~~ one time the attachment coefficient ratio (Ss/Sc), wherein Ss denotes the attachment coefficient of silicon source gas to the silicon carbide substrate at the substrate temperature during formation of said silicon carbide and Sc denotes the attachment coefficient of carbon source gas to the silicon